



SINGLE P-CHANNEL ENHANCEMENT MODE MOSFET

Features

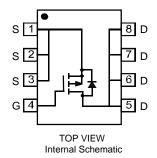
- Low On-Resistance
 - 13mΩ @ V_{GS} = -10V
 - $16m\Omega$ @ $V_{GS} = -4.5V$
 - $22m\Omega$ @ $V_{GS} = -2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072g (approximate)

SO-8





Maximum Ratings @T_A = 25℃ unless otherwise specified

| Characteristic | | | Symbol | Value | Units |
|-------------------------------|--|--|------------------|-----------|-------|
| Drain-Source Voltage | | | V_{DSS} | -20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±12 | V |
| Drain Current (Note 1) | Steady $T_A = 25^{\circ}$ C State $T_A = 70^{\circ}$ C | | I _D | -10 -8 | A |
| Pulsed Drain Current (Note 3) | | | I _{DM} | -35 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|----------------------------------|-------------|------|
| Total Power Dissipation (Note 1) | P _D | 2.5 | W |
| Thermal Resistance, Junction to Ambient | $R_{	heta JA}$ | 50 | €/M |
| Operating and Storage Temperature Range | T _{J,} T _{STG} | -55 to +150 | C |

Notes:

- 1. Device mounted on 2 oz. Copper pads on FR-4 PCB.
- 2. No purposefully added lead.
- 3. Pulse width $\leq 10 \mu S$, Duty Cycle $\leq 1\%$.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

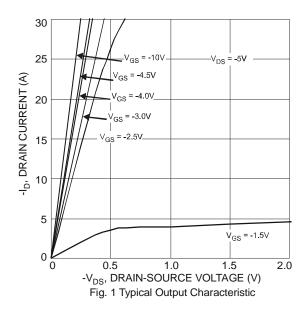


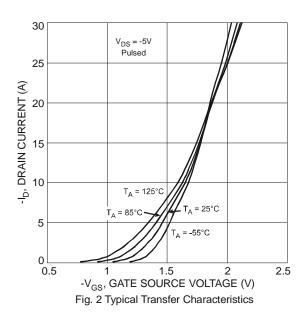
Electrical Characteristics @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|------------------------------------|----------------------|------|--------------|------|------|---|--|
| OFF CHARACTERISTICS (Note 5) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | I | _ | V | $V_{GS} = 0V, I_D = -250\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | | I | -1 | μΑ | $V_{DS} = -20V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | | I | ±100 | nA | $V_{GS} = \pm 12V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 5) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | -0.6 | 0.77 | -1.1 | V | $V_{DS} = V_{GS}, I_D = -250 \mu A$ | |
| | | _ | 8 | 13 | mΩ | $V_{GS} = -10V, I_D = -10A$ | |
| Static Drain-Source On-Resistance | R _{DS (ON)} | _ | 11 | 16 | | $V_{GS} = -4.5V, I_D = -9A$ | |
| | | _ | 17 | 22 | | $V_{GS} = -2.5V, I_D = -8A$ | |
| Forward Transconductance | 9 _{fs} | | 28 | _ | S | $V_{DS} = -10V, I_{D} = -10A$ | |
| Diode Forward Voltage (Note 5) | V_{SD} | -0.5 | 0.68 | -1.2 | V | $V_{GS} = 0V$, $I_S = -3A$ | |
| DYNAMIC CHARACTERISTICS (Note 6) | | | | | | | |
| Input Capacitance | C _{iss} | | 2444 | _ | pF | 101/1/ | |
| Output Capacitance | Coss | _ | 594 | _ | pF | $V_{DS} = -10V, V_{GS} = 0V$ - f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | | 556 | _ | pF | 71 = 1.0WHZ | |
| Gate Resistance | R_{G} | | 2.0 | _ | Ω | $V_{GS} = 0V V_{DS} = 0V, f = 1MHz$ | |
| SWITCHING CHARACTERISTICS (Note 6) | | | | | | | |
| Total Gate Charge | 0 | | 28.1 56.9 | _ | nC | $V_{DS} = -10V$, $V_{GS} = -4.5V$, $I_{D} = -10A$ | |
| Total Gate Gharge | Qg | _ | | | | $V_{DS} = -10V, V_{GS} = -10V, I_{D} = -10A$ | |
| Gate-Source Charge | Q_{gs} | | 3.4 | _ | | $V_{DS} = -10V$, $V_{GS} = -10V$, $I_{D} = -10A$ | |
| Gate-Drain Charge | Q_{gd} | | 11.9 | _ | | $V_{DS} = -10V, V_{GS} = -10V, I_{D} = -10A$ | |
| Turn-On Delay Time | t _{D(on)} | _ | 7.5 | 15 | | | |
| Turn-On Rise Time | t _r | _ | 9.9 | 20 | | $V_{DD} = -15V$, $I_{D} = -1A$, $V_{GS} = -10V$, | |
| Turn-Off Delay Time | t _{D(off)} | _ | 108.0 | 216 | ns | $R_{GEN} = 6\Omega$ | |
| Turn-Off Fall Time | t _f | _ | 76.5 | 153 | | | |

Notes:

- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to product testing.







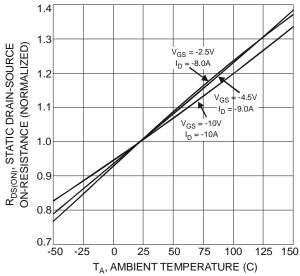
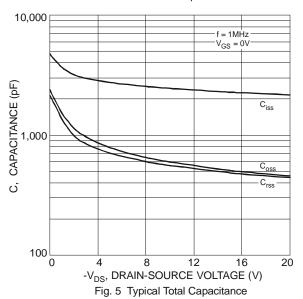


Fig. 3 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



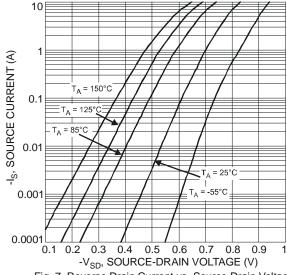


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

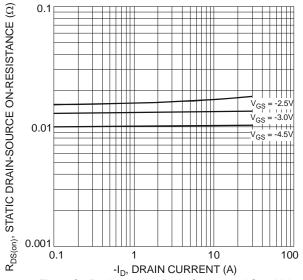


Fig. 4 On-Resistance vs. Drain Current and Gate Voltage

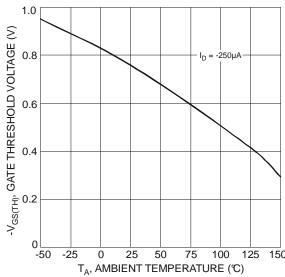


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

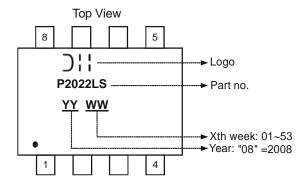


Ordering Information (Note 7)

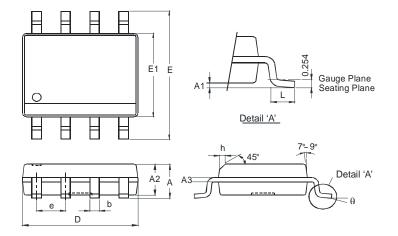
| Part Number | Case | Packaging |
|---------------|------|------------------|
| DMP2022LSS-13 | SO-8 | 2500/Tape & Reel |

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

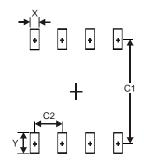


Package Outline Dimensions



| SO-8 | | | | | |
|----------------------|------------|------|--|--|--|
| Dim | Min | Max | | | |
| Α | - | 1.75 | | | |
| A1 | 0.10 | 0.20 | | | |
| A2 | 1.30 | 1.50 | | | |
| А3 | 0.15 | 0.25 | | | |
| b | 0.3 | 0.5 | | | |
| D | 4.85 | 4.95 | | | |
| Е | 5.90 | 6.10 | | | |
| E1 | 3.85 | 3.95 | | | |
| е | e 1.27 Typ | | | | |
| h | - | 0.35 | | | |
| L | 0.62 | 0.82 | | | |
| θ | 0° | 8° | | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Х | 0.60 |
| Υ | 1.55 |
| C1 | 5.4 |
| C2 | 1.27 |



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